



Features

Environments

robust end application

PPAP Capable (Note 4)

Mechanical Data

Case: TO263AB

•

 $\label{eq:low-RDS} \begin{array}{l} \mbox{Low R}_{DS(ON)} - \mbox{Minimizes Power Losses} \\ \mbox{Low Q}_g - \mbox{Minimizes Switching Losses} \end{array}$ 

Flammability Classification Rating 94V-0 Moisture Sensitivity: Level 1 per J-STD-020

Weight: 1.7 grams (Approximate)

Solderable per MIL-STD-202, Method 208 @3

Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

## DMTH4004SCTBQ

#### 40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Rated to +175°C - Ideal for High Ambient Temperature

100% Unclamped inductive switching ensures more reliable and

Case Material: Molded Plastic, "Green" Molding Compound; UL

Terminal Finish - Matte Tin Annealed over Copper Leadframe.

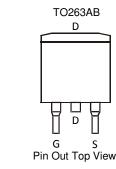
#### **Product Summary**

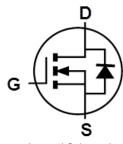
BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Q <sub>g</sub> Тур	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 10)
40V	3mΩ @ V <sub>GS</sub> = 10V	68.6nC	100A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters





Internal Schematic

### Ordering Information (Note 5)

Top View

Part Number	Case	Packaging
DMTH4004SCTBQ-13	TO263AB	800/Tape & Reel

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

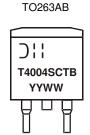
4. Automotive products are AEC-Q101 qualified and are PPAP capable. For more information, please refer to

http://www.diodes.com/product\_compliance\_definitions.html.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

Notes:



T4004SCTB = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 14 = 2014) WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V <sub>DSS</sub>	40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7)	T <sub>C</sub> = +25°C (Note 10)	ID	100	А
	$T_{\rm C} = +100^{\circ}{\rm C}$	D	100	
Maximum Continuous Body Diode Forward Current		ls	100	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	200	A	
Avalanche Current, L=0.2mH	IAS	45	A	
Avalanche Energy, L=0.2mH		Eas	200	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	PD	4.7	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ heta JA}$	32	°C/W
Total Power Dissipation (Note 7)	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	136	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.1	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

			_				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—		V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	2.5	3	mΩ	$V_{GS} = 10V, I_D = 100A$	
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.3	V	$V_{GS} = 0V, I_{S} = 100A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	4,305	_		$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	1,441	_	pF		
Reverse Transfer Capacitance	Crss	_	102	_			
Gate Resistance	R <sub>G</sub>	_	0.77	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	—	68.6	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ I_D = 90A, \\ V_{GS} &= 10V \end{split}$	
Gate-Source Charge	Q <sub>gs</sub>	—	16.8	_	nC		
Gate-Drain Charge	Q <sub>gd</sub>	_	14.2	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	9.5	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ V_{GS} = 10V, \\ I_D &= 90A, \ R_G = 3.5\Omega \end{split}$	
Turn-On Rise Time	t <sub>R</sub>	_	6.7				
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	26.4		ns		
Turn-Off Fall Time	tF	—	8.1				
Reverse Recovery Time	t <sub>RR</sub>	—	52.4		ns		
Reverse Recovery Charge	Q <sub>RR</sub>	_	78.2		nC	I <sub>F</sub> = 50A, di/dt = 100A/μs	

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

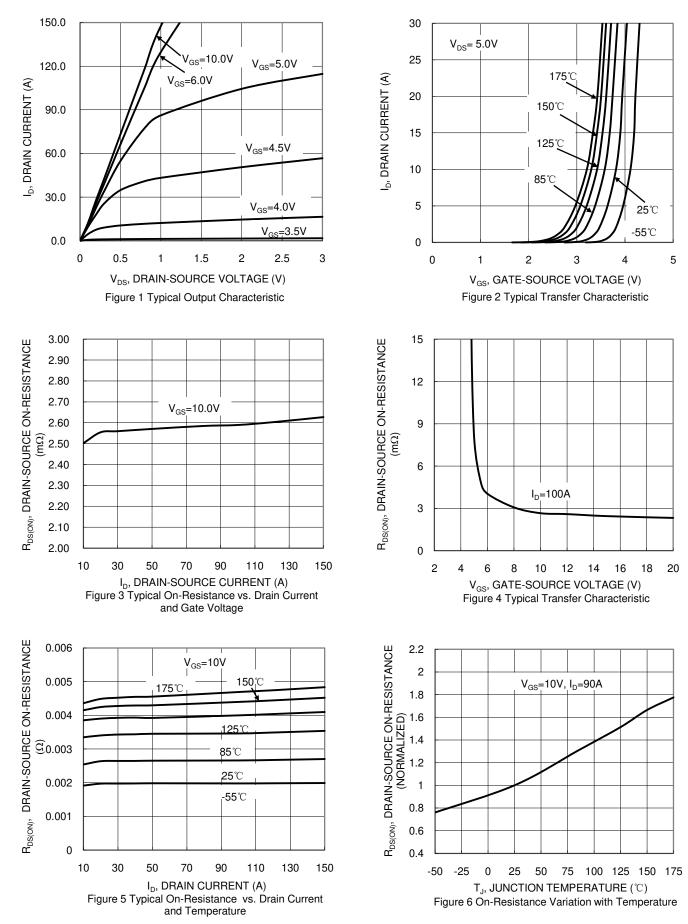
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

10. Package limited.



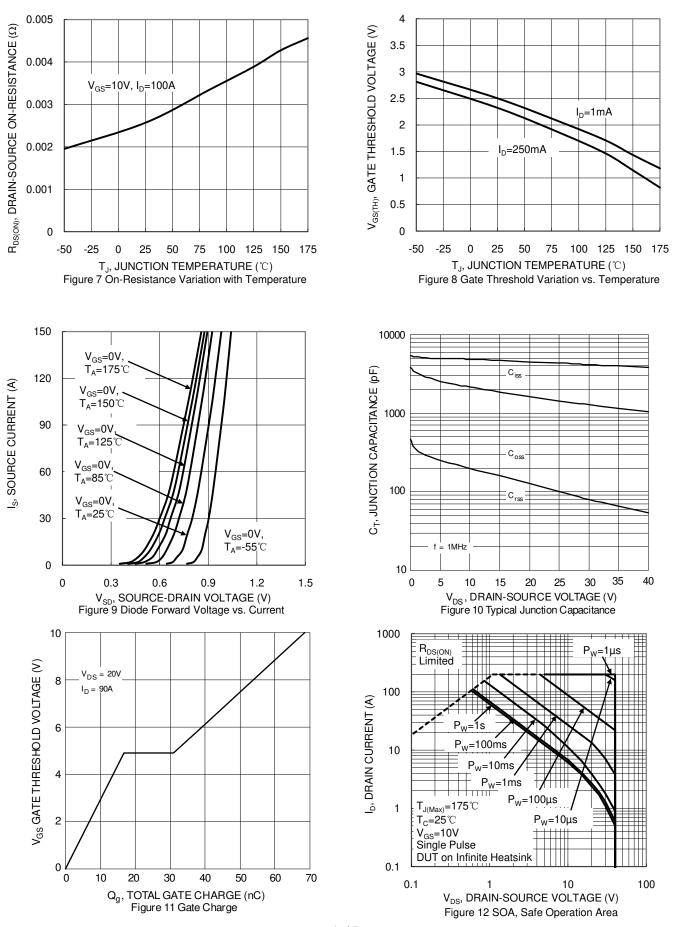
## DMTH4004SCTBQ



DMTH4004SCTBQ Document number: DS37796 Rev. 2 - 2 3 of 7 www.diodes.com

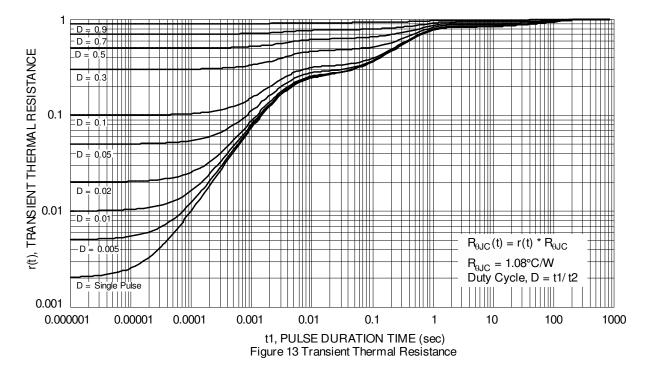


## DMTH4004SCTBQ



DMTH4004SCTBQ Document number: DS37796 Rev. 2 - 2 November 2015 © Diodes Incorporated



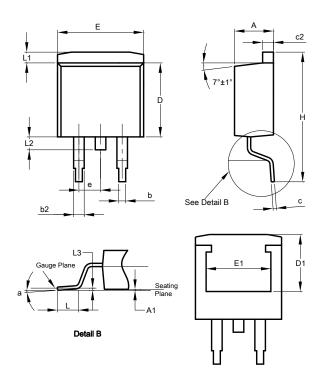




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### TO263AB (D2PAK)

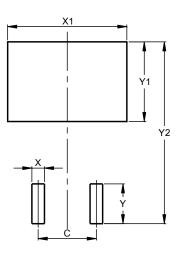


то	TO263AB (D2PAK)					
Dim	Min	Max	Тур			
Α	4.07	4.82	-			
A1	0.00	0.25	-			
b	0.51	0.99	-			
b2	1.15	1.77	-			
С	0.356	0.73	-			
c2	1.143	1.65	-			
D	8.39	9.65	-			
D1	6.55	6.95	-			
е		2.54 TYP				
E	9.66	10.66	-			
E1	6.23	8.23	-			
Н	14.61	15.87	-			
L	1.78	2.79	-			
L1	-	1.67	-			
L2	-	1.77	-			
L3	-	-	0.254			
а	0°	8°	-			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### TO263AB (D2PAK)



Dimensions	Value (in mm)			
С	5.08			
Х	1.10			
X1	10.41			
Y	3.50			
Y1	7.01			
Y2	15.99			



#### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com